ADE-208-179A(Z)

1SS110
Silicon Epitaxial Planar Diode for Tuner Band Switch

HITACHI

Rev. 1
Nov. 1994

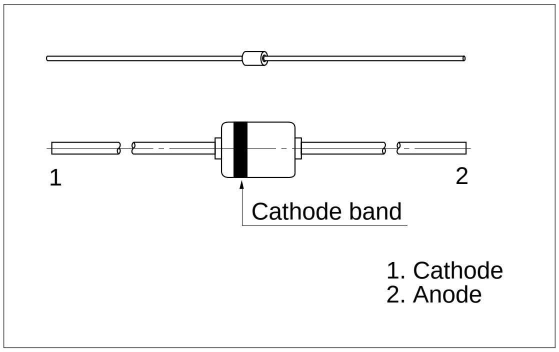
Features

- Low forward resistance. (r_f = 0.9Ω max)
- Suitable for 5mm pitch high speed automatical insertion.
- Small glass package (MHD) enables easy mounting and high reliability.

Ordering Information

Type No.	Cathode band	Package Code
1SS110	Verdure	MHD

Outline



Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Reverse voltage	V_R	35	V
Forward current	I_F	100	mA
Power dissipation	P_d	15 0	mW
Operation temperature	T_{opr}	-20 to + 60	°C
Storage temperature	T_{stg}	-55 to +150	°C

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_F	—	—	1.0	V	I_F = 10 mA
Reverse voltage	V_R	35	—	—	V	I_R = 10 µA
Reverse current	I_R	—	—	0.1	µA	V_R = 25 V
Capacitance	C	—	—	1.2	pF	V_R = 6 V , f = 1 MHz
Forward resistance	r_f	—	—	0.9	Ω	I_F = 2 mA , f = 100 MHz

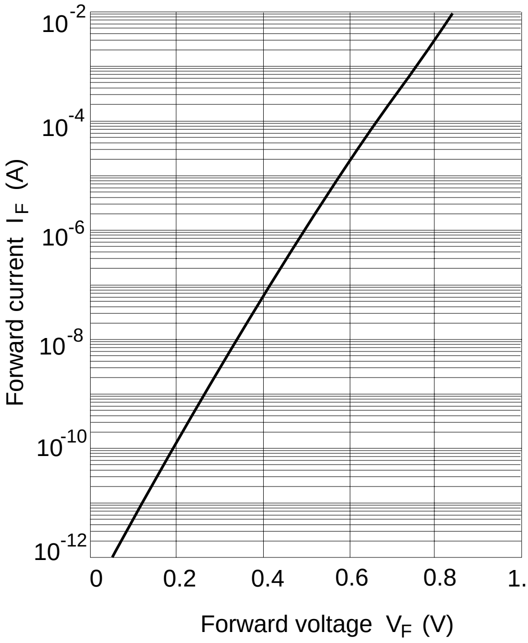


Fig.1 Forward current Vs. Forward voltage

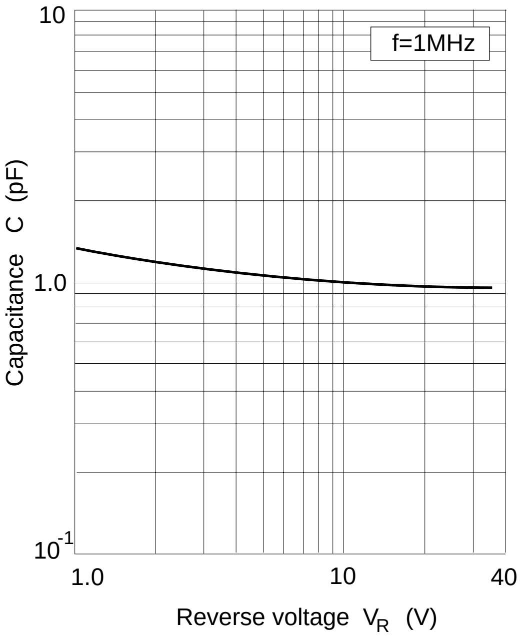


Fig.2 Capacitance Vs. Reverse voltage

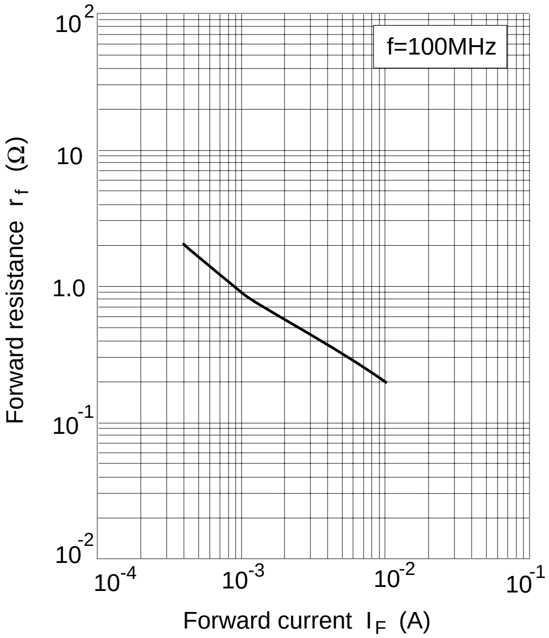
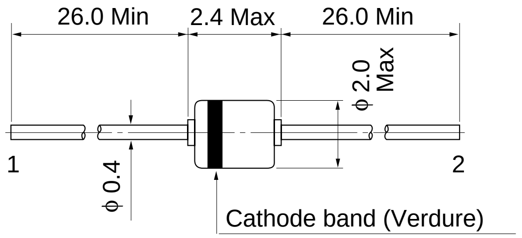


Fig.3 Forward resistance Vs. Forward current

Package Dimensions

Unit: mm



1 Cathode
2 Anode

HITACHI Code	MHD
JEDEC Code	DO-34
EIAJ Code	—
Weight (g)	0.084